

Name :

Roll No. :

Invigilator's Signature :

CS/M.TECH(EIE)/SEM-1/EIEM-101/2011-12

2011

ADVANCED ELECTRONICS CIRCUITS

Time Allotted : 3 Hours

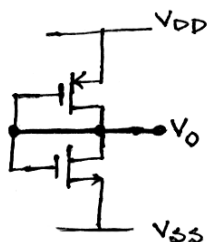
Full Marks : 70

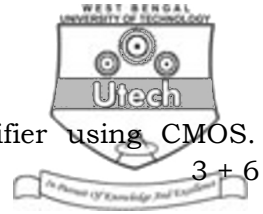
The figures in the margin indicate full marks.

*Candidates are required to give their answers in their own words
as far as practicable.*

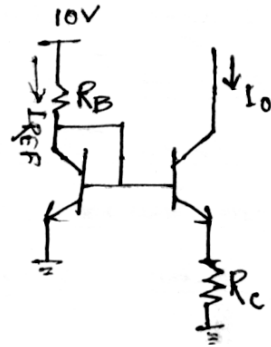
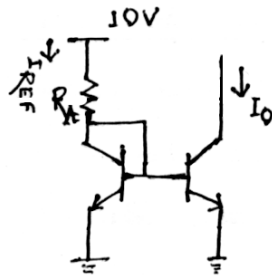
Answer any **five** questions. $5 \times 14 = 70$

1. a) Using MOS (both *N*-channel & *P*-channel) draw the equivalent of active resistors. Find out the expression for current & channel conductance. Draw the small signal model. 3 + 4 + 2
- b) The MOSFETs (in the following figure) are used for voltage division. Find W/L ratio for both the MOSFETs that give V_0 of 1 V, if $V_{DD} = +5$ V, $V_{SS} = -5$ V and $I = 100$ μ A. Assume that $V_{TN} = 0.75$ V, $V_{TP} = -0.75$ V, $K'_N = 2.4 \times 10^{-5}$ A/V², $K'_P = 0.8 \times 10^{-5}$ A/V². 5

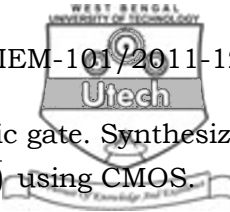




2. a) Draw the ckt for differential amplifier using CMOS. Hence, find the value of A_{vds} . 3 + 6
- b) Draw the small signal for two stage operational amplifier using BJT. 5
3. a) Why constant current source biasing is used in I.C. design ? Analyse the Widlar current source and obtain expressions for
 - i) output current and
 - ii) output resistance of this source. 2 + 6
- b)



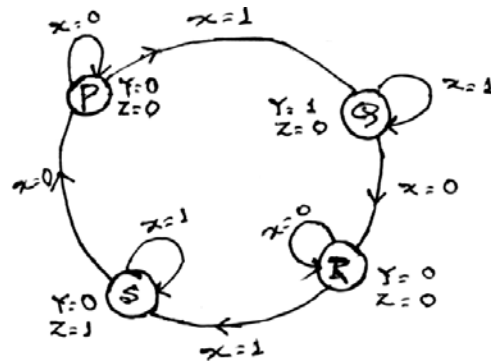
The above two ckts are for generating a constant current $I_0 = 10 \mu A$ which operate from a 10 V supply. Determine the value of all resistors. Assume $V_T = 0.25 V$. 6



4. a) Draw the basic structure of CMOS logic gate. Synthesize the Boolean function $F = \overline{A + B(C + D)}$ using CMOS. 2 + 7
- b) What is meant by transistor sizing and how is it done ? TWO MOSFETs having aspect ratio of $(W/L)_1$ and $(W/L)_2$ are connected in series. Determine the equivalent aspect ratio of this series combination. 3 + 2
5. a) Draw an 8-bit voltage scaling D/A converter and explain its operation with the $i/p-o/p$ characteristic curve. 2 + 5 + 2
- b) Find the accuracy requirement for a resistor string consisting of N equal segments as a function of the number of bits N . If the relative resistor accuracy is 5%, what is the largest no. of bits that can be resolved to within ± 0.5 LSB ? 5
6. a) Explain with the help of circuit diagram the CMOS implementation of a clocked S.R. flip-flop. 9
- b) Using two-phase non-overlapping clock implement D-flip-flop. 5
7. a) Explain the importance of propagation delay and power dissipation in the logic circuit design. Draw the circuit diagram of a CMOS inverter and with reference to its voltage transfer characteristic obtain the matching condition. 3 + 2 + 5
- b) What are the advantages that result from matching ? 4



8. For the following state diagram design a clocked PLA FSM where x is the i/p and Y & Z are the o/p 's.



9. Write short notes on any *two* of the following : 2 × 7

- IC fabrication process
- Bi CMOS inverter
- Charge distribution converter
- Current mirror.

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